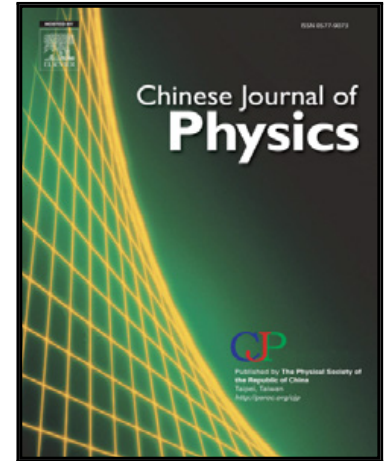


## Accepted Manuscript

Effect of the built-in electric field on electron Raman scattering of parabolic  $In_xGa_{1-x}N/GaN$  quantum dot

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## Highlights

- Raman spectra is proposed for  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  quantum dot with effective mass approach.
- Various built-in electric field accounts for energy shift of the spectrum.
- As built-in electric field increases, FWHM of spectrum decreases.

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